

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	100.00 +/- 0.30 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 deg	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	Wafer Vendor
	5.0	Overall Thickness	856.00 +/- 1.00 μ m	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<1.00 μ m	Guaranteed by Process
	7.0	SFQR	<1.00 μ m	ADE 1005, site size 20mm x 20mm, no partials
	8.0	Bow	<40.00 μ m	ADE to ASTM F534, 20%
	9.0	Warp	<40.00 μ m	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{111} off 2.5 +/- 0.5 degree	Wafer Vendor
	14.0	Handle Thickness	825.00 +/- 2.00 μ m	ADE, 100%
	15.0	Handle Doping Type	N	Wafer Vendor
	16.0	Handle Dopant	Arsenic	Wafer Vendor
	17.0	Handle Resistivity	0.001 - 0.004 Ohm cm	Wafer Vendor
	18.0	Backside Finish	Polished with no oxide	Wafer Vendor
	DeviceSilicon	19.0	Device Growth Method	FZ
20.0		Device Orientation	{111} off 3.5 +/- 1 degree	Wafer Vendor
21.0		Nominal Thickness	25.00 +/- 1.00 μ m	FTIR, 100% 9-Pt (note3)
22.0		Distance to device silicon edge from wafer edge	<= 3mm	Typical by Process
23.0		Device Doping Type	N	Wafer Vendor
24.0		Device Dopant	Phosphorous	Wafer Vendor
25.0		Device Resistivity	> 5000 Ohm-cm	Wafer Vendor
26.0		Voids	none (by SAM measurement)	100% CSAM inspection
27.0		Surface	polished prime	Bright light inspection 100%
28.0		Scratches	none	Bright Light, 100% (note 2)
29.0		Haze	none	Bright Light, 100% (note 2)
30.0		LPD Count	<15.00pcs	particles 0.5 -1.0 μ m by Tencor 6220

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Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information